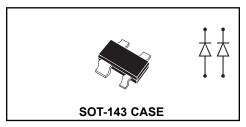


DUAL, ISOLATED HIGH CURRENT SILICON SWITCHING DIODES



MAXIMUM RATINGS: (T_A=25°C)



DESCRIPTION:

The CENTRAL SEMICONDUCTOR BAS56 consists of two electrically isolated ultra-high speed silicon switching diodes manufactured by the epitaxial planar process and packaged in an epoxy molded surface mount SOT-143 case. This device is designed for high speed switching applications.

MARKING CODE: L51

| | SYMBOL | | UNITS |
|---------------------------------|----------------------------------|-------------|-------|
| Continuous Reverse Voltage | VR | 60 | V |
| Peak Repetitive Reverse Voltage | V _{RRM} | 60 | V |
| Continuous Forward Current | ١F | 200 | mA |
| Peak Repetitive Forward Current | IFRM | 400 | mA |
| Forward Surge Current, tp=1 µs | IFSM | 4.0 | А |
| Forward Surge Current, tp=1 s | IFSM | 1.0 | А |
| Power Dissipation | PD | 350 | mW |
| Operating and Storage | | | |
| Junction Temperature | T _J ,T _{stg} | -65 to +150 | °C |
| Thermal Resistance | Θ_{JA} | 357 | °C/W |

ELECTRICAL CHARACTERISTICS PER DIODE: (T_A=25°C unless otherwise noted)

| SYMBOL | TEST CONDITIONS | MIN | MAX | UNITS |
|-----------------|--|-----|------|-------|
| I _R | V _R =60V | | 100 | nA |
| I _R | V _R =60V, T _A =150°C | | 100 | μA |
| I _R | V _R =75V | | 10 | μA |
| VF | I _F =10mA | | 0.75 | V |
| VF | IF=200mA | | 1.0 | V |
| VF | IF=500mA | | 1.25 | V |
| CT | V _R =0, f=1.0 MHz | | 2.5 | pF |
| t _{rr} | $I_F=I_R=400$ mA, RL=100 Ω , Rec. to 40mA | | 6.0 | ns |
| Qs | I _F =10mA, V _R =5.0V, R _L =500Ω | | 50 | рС |
| V _{FR} | I _F =400mA, t _r =30ns | | 1.2 | V |
| V _{FR} | I _F =400mA, t _r =100ns | | 1.5 | V |

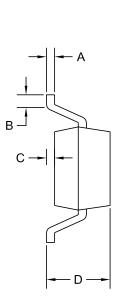
R4 (3-December 2003)

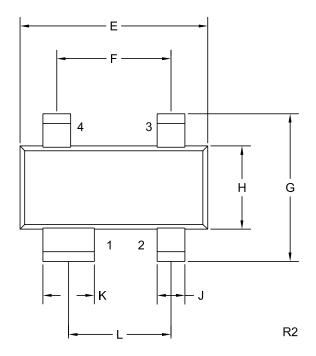


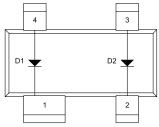
BAS56

DUAL, ISOLATED HIGH CURRENT SILICON SWITCHING DIODES

SOT-143 CASE - MECHANICAL OUTLINE







LEAD CODE:

1) CATHODE D1 2) CATHODE D2 3) ANODE D2 4) ANODE D1

MARKING CODE: L51

DIMENSIONS INCHES MILLIMETERS SYMBOL MIN MAX MIN MAX 0.006 0.08 А 0.003 0.15 В 0.006 0.15 --С 0.005 0.13 D 0.045 1,14 0.110 0.120 2.79 Е 3.04 F 0.075 1.90 0.098 G 2.50 --Н 0.047 0.055 1.19 1.40 J 0.014 0.020 0.36 0.50 Κ 0.030 0.037 0.76 0.93 0.067 1.70 SOT-143 (REV: R2)

R4 (3-December 2003)